

**STE70NM50****N-CHANNEL 500V - 0.045Ω - 70A ISOTOP  
Zener-Protected MDmesh™ Power MOSFET**

TYPE	V <sub>DSS</sub>	R <sub>D(on)</sub>	I <sub>D</sub>
STE70NM50	500V	< 0.05Ω	70 A

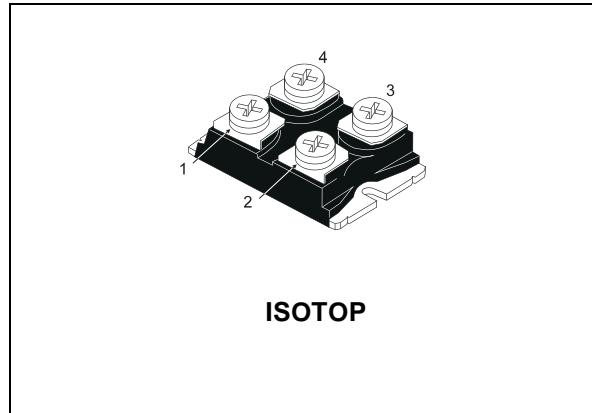
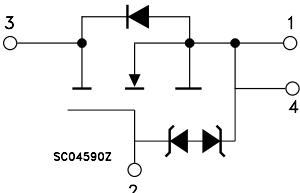
- TYPICAL R<sub>D(on)</sub> = 0.045Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- IMPROVED ESD CAPABILITY
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE
- TIGHT PROCESS CONTROL
- INDUSTRY'S LOWEST ON-RESISTANCE

**DESCRIPTION**

The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

**APPLICATIONS**

The MDmesh™ family is very suitable for increasing power density of high voltage converters allowing system miniaturization and higher efficiencies.

**ISOTOP****INTERNAL SCHEMATIC DIAGRAM****ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	500	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	500	V
V <sub>GS</sub>	Gate- source Voltage	±30	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	70	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	44	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	280	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	600	W
V <sub>ESD(G-S)</sub>	Gate source ESD(HBM-C=100pF, R=15kΩ)	6	kV
	Derating Factor	5	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	15	V/ns
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C

(•)Pulse width limited by safe operating area

(1)I<sub>D</sub> ≤ 60A, di/dt ≤ 400A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>

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## STE70NM50

### THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	0.2	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	30	°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		300	°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	30	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 35 V)	1.4	J

### ELECTRICAL CHARACTERISTICS (T<sub>CASE</sub> = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	500			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			10 100	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20V			± 10	μA

### ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	3	4	5	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A		0.045	0.05	Ω

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> , I <sub>D</sub> = 30A		35		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		7500		pF
C <sub>oss</sub>	Output Capacitance			980		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			200		pF
R <sub>G</sub>	Gate Input Resistance	f=1 MHz Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.5		Ω

Note: 1. Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.

**ELECTRICAL CHARACTERISTICS (CONTINUED)**  
**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 250V, I_D = 30A$		51		ns
$t_r$	Rise Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		58		ns
$Q_g$	Total Gate Charge	$V_{DD} = 400V, I_D = 60A,$		190	266	nC
$Q_{gs}$	Gate-Source Charge	$V_{GS} = 10V$		53		nC
$Q_{gd}$	Gate-Drain Charge			97		nC

**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(loff)}$	Off-voltage Rise Time	$V_{DD} = 400V, I_D = 60A,$		51		ns
$t_f$	Fall Time	$R_G = 4.7\Omega, V_{GS} = 10V$		46		ns
$t_c$	Cross-over Time	(see test circuit, Figure 5)		108		ns

**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				60	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				240	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 60A, V_{GS} = 0$			1.5	V
$t_{rr}$ $Q_{rr}$ $I_{rrm}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 60A, di/dt = 100A/\mu s, V_{DD} = 100V, T_j = 25^\circ C$ (see test circuit, Figure 5)		532 9.9 37		ns $\mu C$ A
$t_{rr}$ $Q_{rr}$ $I_{rrm}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 60A, di/dt = 100A/\mu s, V_{DD} = 100V, T_j = 150^\circ C$ (see test circuit, Figure 5)		636 13.4 42		ns $\mu C$ A

Note: 1. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %.  
 2. Pulse width limited by safe operating area.

**GATE-SOURCE ZENER DIODE**

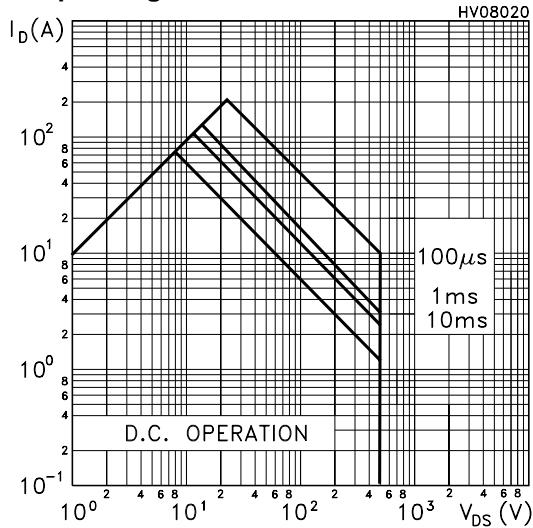
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$BV_{GSO}$	Gate-Source Breakdown Voltage	$I_{GS} = \pm 1mA$ (Open Drain)	30			V

**PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES**

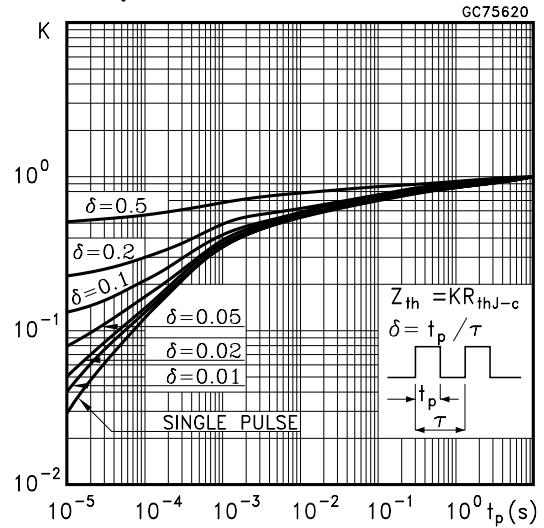
The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the 25V Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

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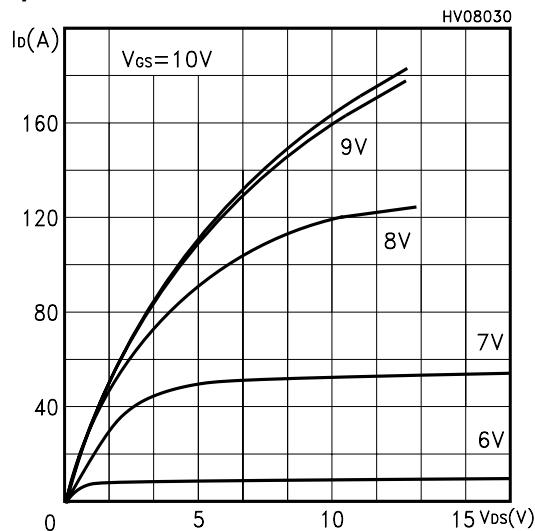
### Safe Operating Area



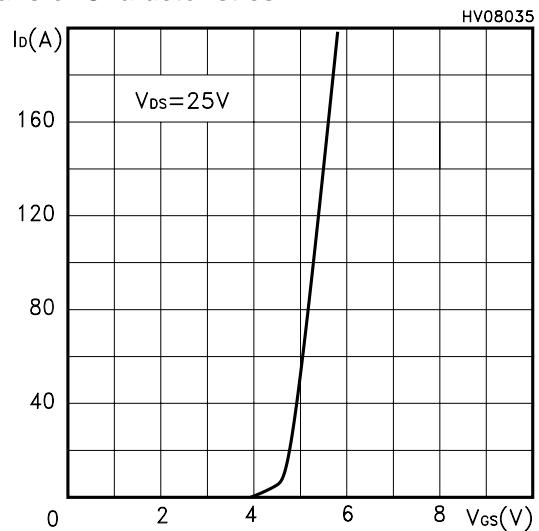
### Thermal Impedance



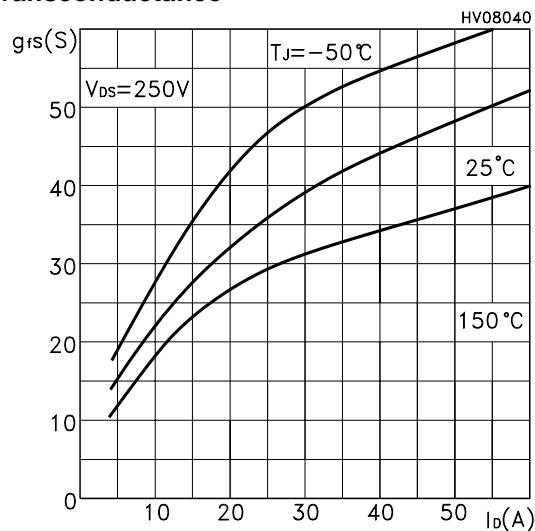
### Output Characteristics



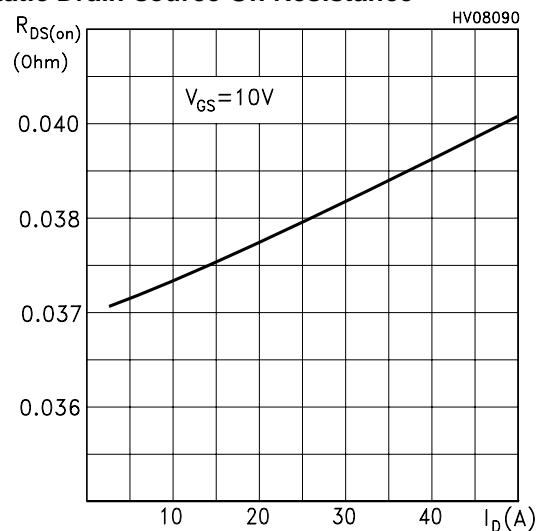
### Transfer Characteristics

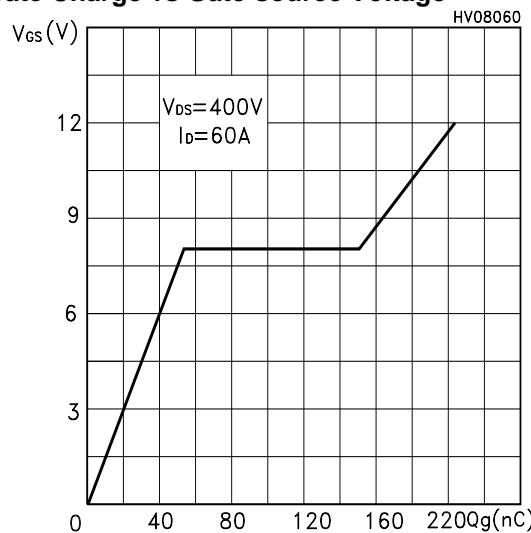
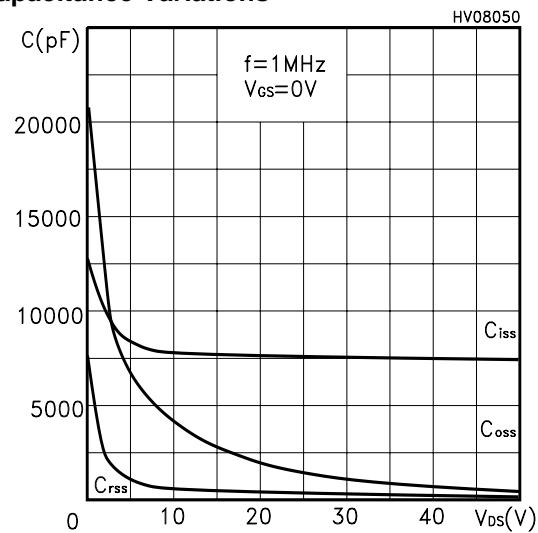
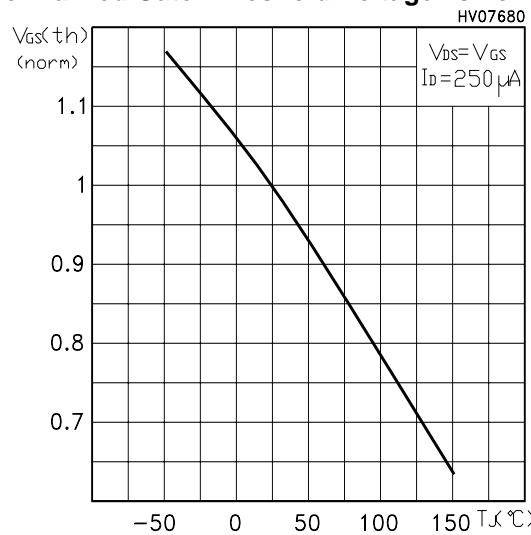
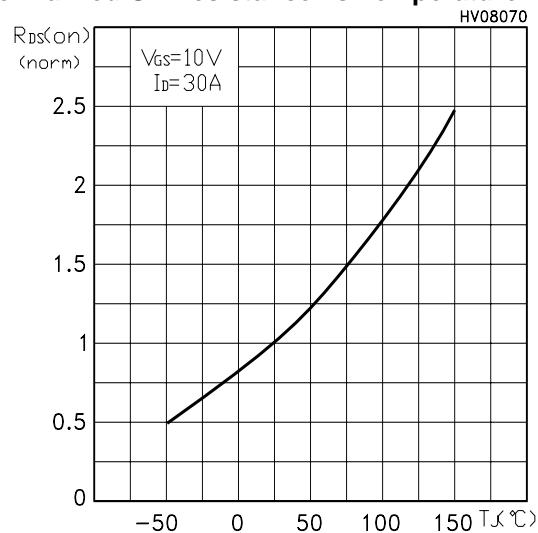
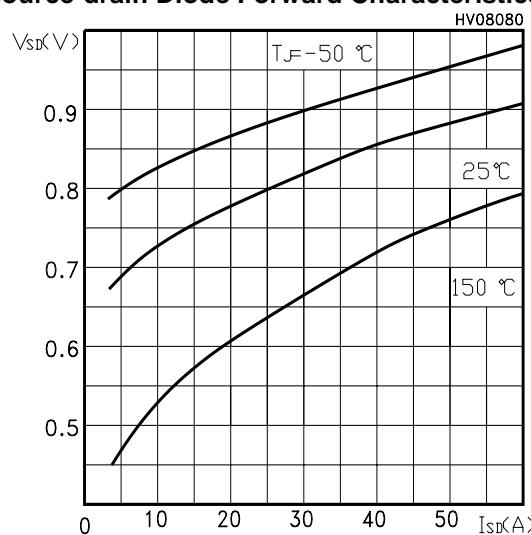


### Transconductance



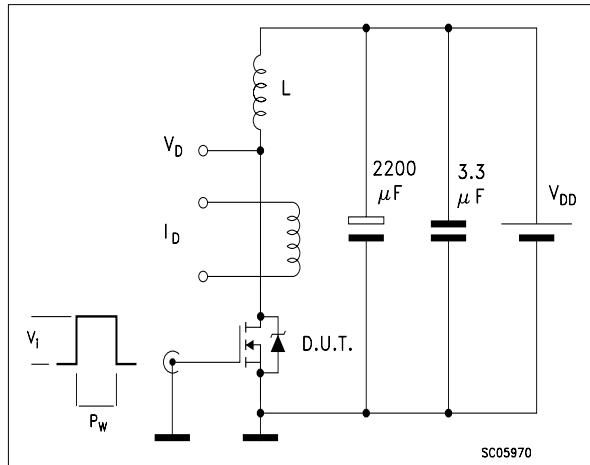
### Static Drain-source On Resistance



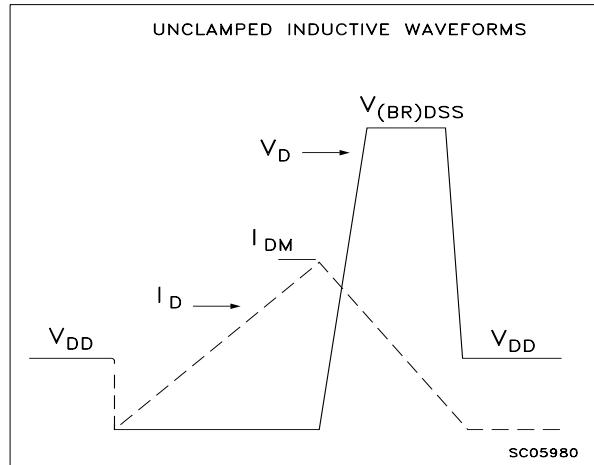
**Gate Charge vs Gate-source Voltage****Capacitance Variations****Normalized Gate Threshold Voltage vs Temp.****Normalized On Resistance vs Temperature****Source-drain Diode Forward Characteristics**

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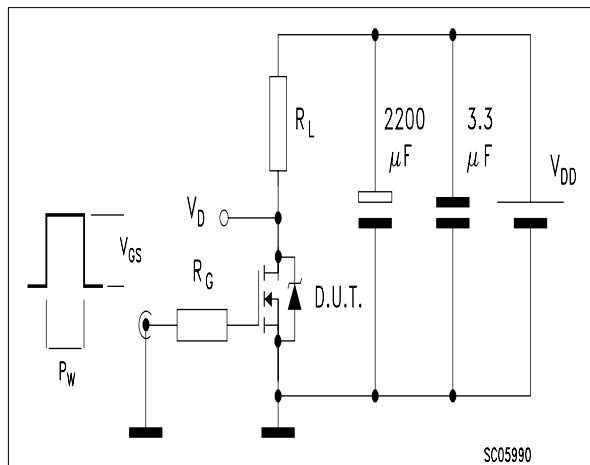
**Fig. 1: Unclamped Inductive Load Test Circuit**



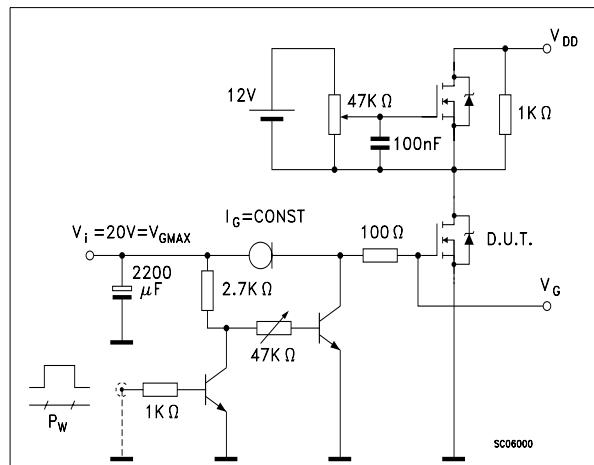
**Fig. 2: Unclamped Inductive Waveform**



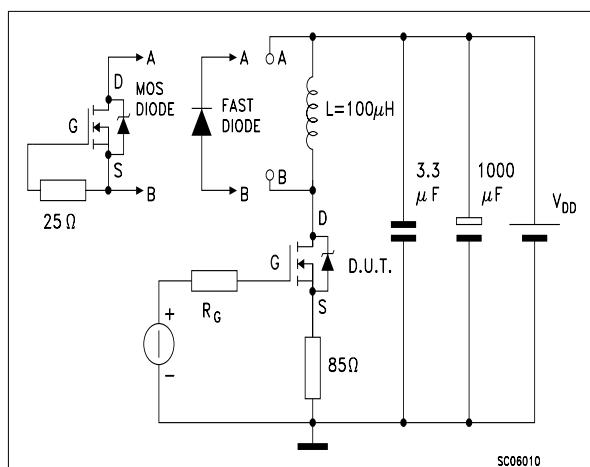
**Fig. 3: Switching Times Test Circuit For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

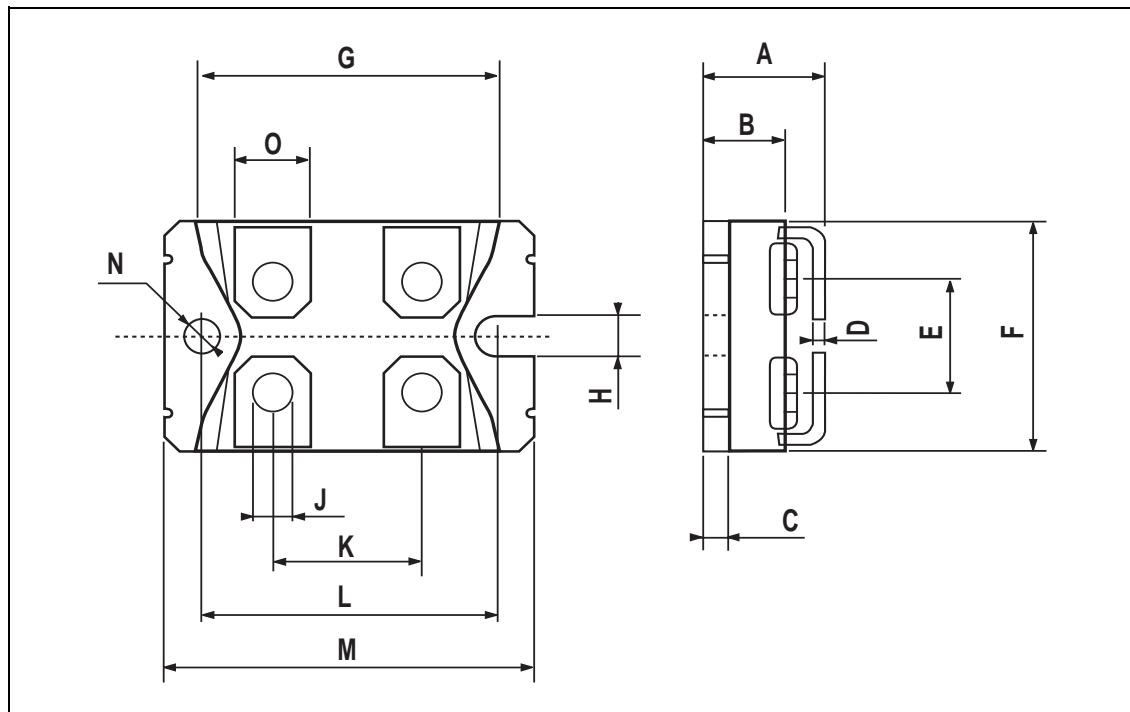


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



## ISOTOP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.8		12.2	0.466		0.480
B	8.9		9.1	0.350		0.358
C	1.95		2.05	0.076		0.080
D	0.75		0.85	0.029		0.033
E	12.6		12.8	0.496		0.503
F	25.15		25.5	0.990		1.003
G	31.5		31.7	1.240		1.248
H	4			0.157		
J	4.1		4.3	0.161		0.169
K	14.9		15.1	0.586		0.594
L	30.1		30.3	1.185		1.193
M	37.8		38.2	1.488		1.503
N	4			0.157		
O	7.8		8.2	0.307		0.322



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